General Description

The WSD20L120ADN56 is the highest performance trench P-Channel MOSFET with extreme high cell density, which provide excellent $R_{DS(ON)}$ and gate charge for most of the synchronous buck converter applications.

The WSD20L120ADN56 meet the RoHS and Green Product requirement 100% E_{AS} guaranteed with full function reliability approved.

Features

- Advanced high cell density Trench technology
- Super Low Gate Charge
- Excellent CdV/dt effect decline
- 100% E_{AS} Guaranteed
- Green Device Available

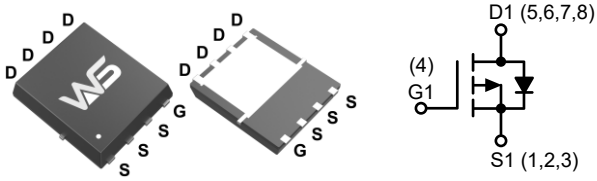
Product Summery

BV_{DSS}	$R_{DS(ON)}$	I_D
-20V	4.0mΩ	-88A

Applications

- High Frequency Point-of-Load Synchronous Buck Converter for MB/NB/UMPC/VGA
- Networking DC-DC Power System
- Load Switch

DFN5X6-8L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	-20	V
V_{GS}	Gate-Source Voltage	±10	
I_D@T_C=25°C	Continuous Drain Current, V_{GS} @ -10V [1]	-88	A
I_D@T_C=100°C	Continuous Drain Current, V_{GS} @ -10V [1]	-45	
I_{DM}	Pulsed Drain Current [2]	-310	
E_{AS}	Single Pulse Avalanche Energy [3]	80	mJ
I_{AS}	Avalanche Current	-40	A
P_D@T_C=25°C	Total Power Dissipation [4]	52	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	

Thermal Data

Symbol	Parameter	Typ.	Max.	Units
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [1]	---	62	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient [1] (t ≤10s)	---	50	
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case [1]	---	2.4	

Electrical Characteristics (T_J=25°C, Unless Otherwise Noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V , I_D=-250μA	-20	---	---	V
$\Delta BV_{DSS}/\Delta T_J$	BV_{DSS} Temperature Coefficient	Reference to 25°C, I_D=-1mA	---	-0.0212	---	V/°C
$R_{DS(ON)}$	Static Drain-Source On-Resistance [2]	V_{GS}=-4.5V , I_D=-25A	---	4.0	5.0	mΩ
		V_{GS}=-2.5V , I_D=-20A	---	5.5	7.5	
$V_{GS(th)}$	Gate Threshold Voltage	V_{GS}=V_{DS} , I_D=-250μA	-0.4	-0.6	-1.0	V
$\Delta V_{GS(th)}$	$V_{GS(th)}$ Temperature Coefficient		---	4.8	---	mV/°C
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-20V , V_{GS}=0V , T_J=25°C	---	---	-1.0	μA
		V_{DS}=-20V , V_{GS}=0V , T_J=55°C	---	---	-6.0	
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±10V , V_{DS}=0V	---	---	±100	nA
g_{fs}	Forward Transconductance	V_{DS}=-5V , I_D=-20A	---	30	---	S
R_g	Gate Resistance	V_{DS}=0V , V_{GS}=0V , f = 1.0MHz	---	1.5	2.5	Ω
Q_g	Total Gate Charge(-4.5)	V_{DS}=-10V , V_{GS}=-4.5V , I_D=-20A	---	32	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	7	---	
$T_{d(on)}$	Turn-On Delay Time	V_{DD}=-10V , V_{GEN}=-4.5V , R_G=3Ω , I_D=-1A , R_L=0.5Ω	---	12	---	ns
T_r	Rise Time		---	10	---	
$T_{d(off)}$	Turn-Off Delay Time		---	85	---	
T_f	Fall Time		---	34	---	
C_{iss}	Input Capacitance	V_{DS}=-10V , V_{GS}=0V , f = 1.0MHz	---	3350	---	pF
C_{oss}	Output Capacitance		---	360	---	
C_{rss}	Reverse Transfer Capacitance		---	230	---	

Diode Characteristics

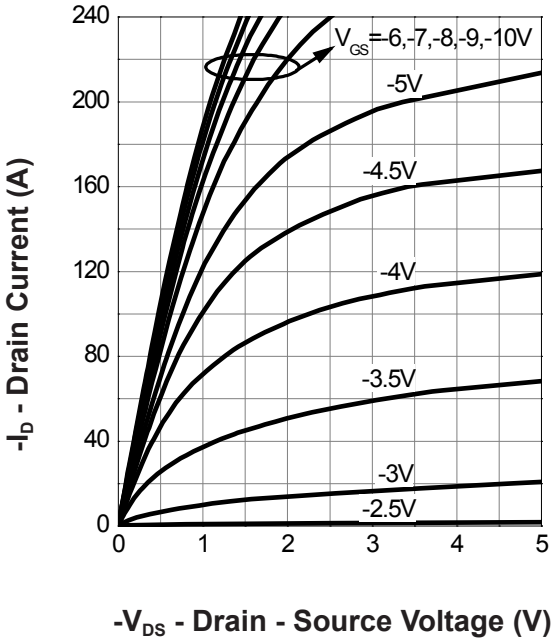
Symbol	Parameter	Conditions	Min.	Typ.	Max.	Units
I_S	Continuous Source Current [1,6]	V_G=V_D=0V , Force Current	---	---	-88	A
I_{SM}	Pulsed Source Current [2,6]		---	---	310	
V_{SD}	Diode Forward Voltage [2]	V_{GS}=0V , I_S=-1A , T_J=25°C	---	---	-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-15A,dI/dt=100A/μs,T_J=25°C	---	30	---	ns
Q_{rr}	Reverse Recovery Charge		---	25	---	nC

Note:

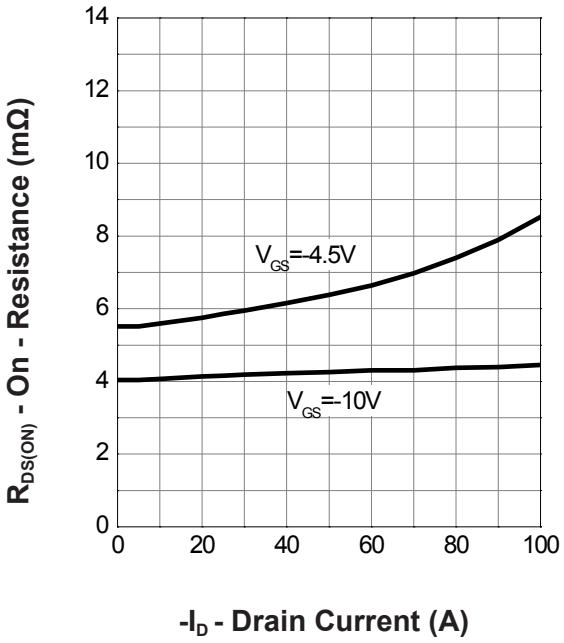
1. The data tested by surface mounted on a 1 inch^2 FR-4 board with 2OZ copper,t≤10sec.
2. The data tested by pulsed , pulse width ≤ 300μs , duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating . The test condition is V_{DD}=-10V, V_{GS}=-10V, L=0.1mH, I_{AS}=-40A
4. The power dissipation is limited by 150°C junction temperature.
5. The Min. value is 100% E_{AS} tested guarantee.
6. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

Typical Characteristics

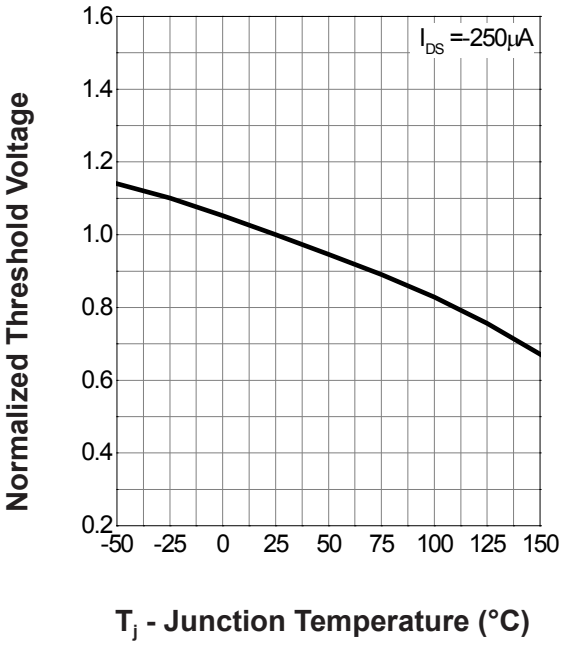
Output Characteristics



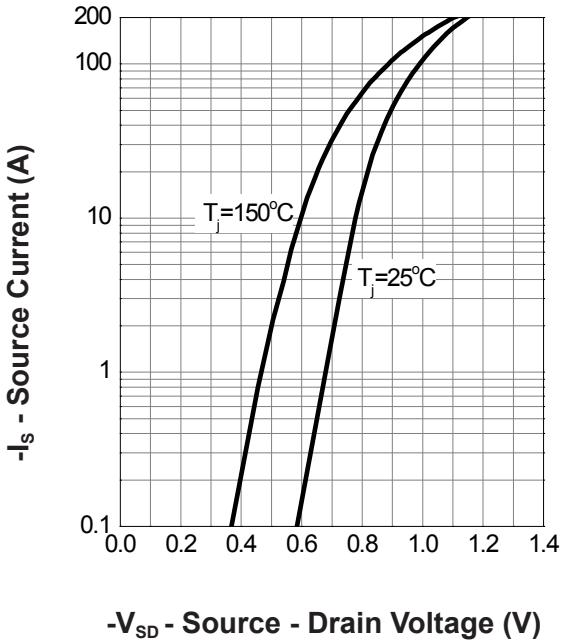
Drain-Source On Resistance



Gate Threshold Voltage

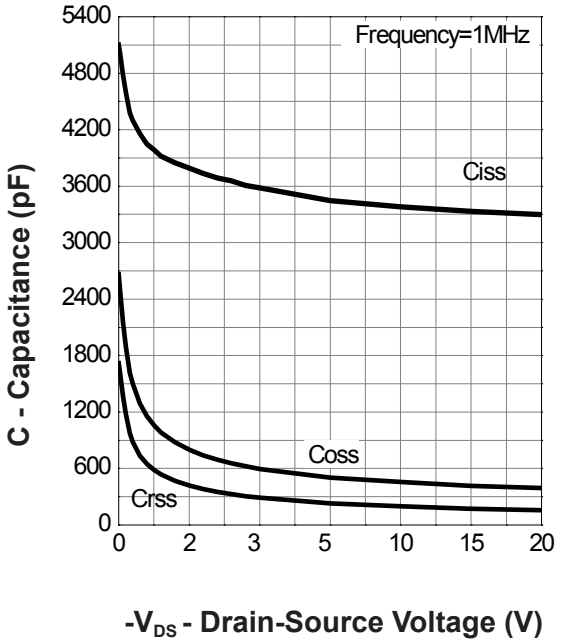


Source-Drain Diode Forward

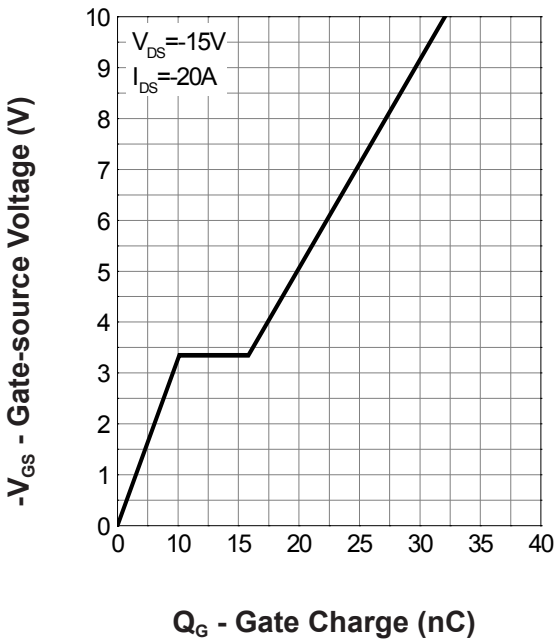


Typical Characteristics (Cont.)

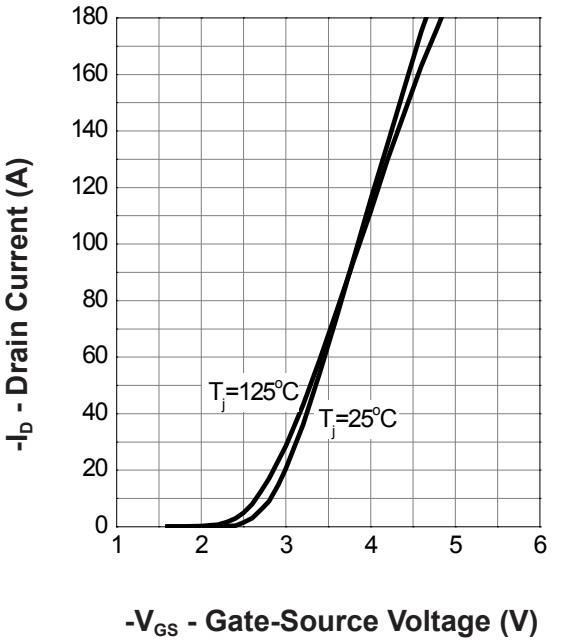
Capacitance



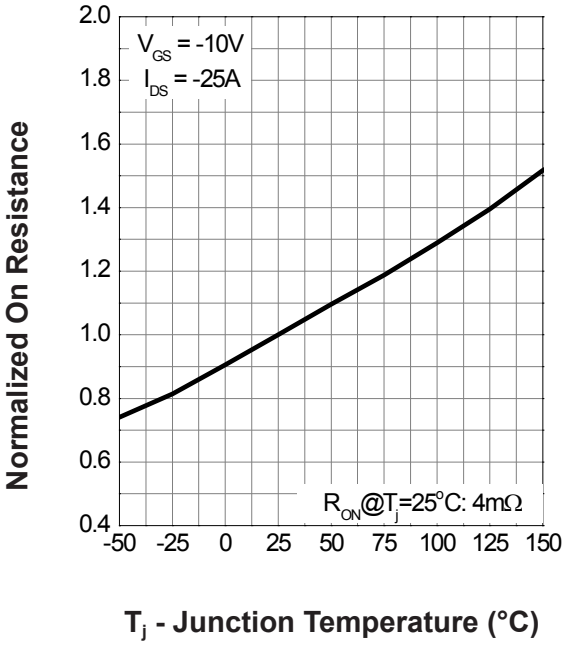
Gate Charge



Transfer Characteristics

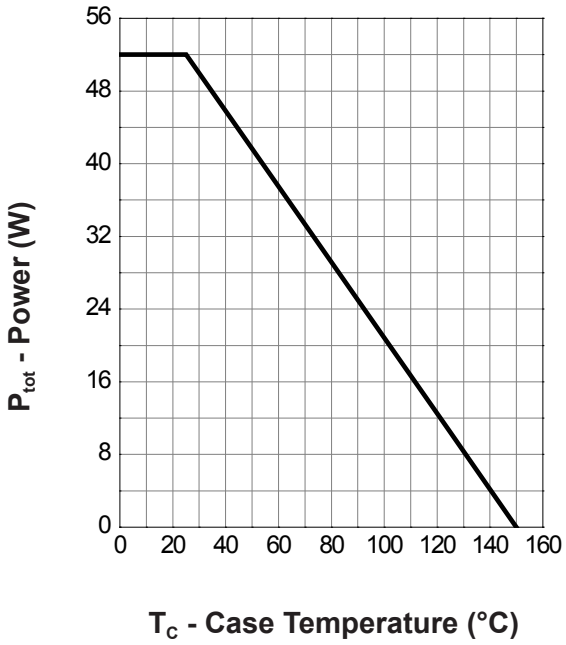


Drain-Source On Resistance

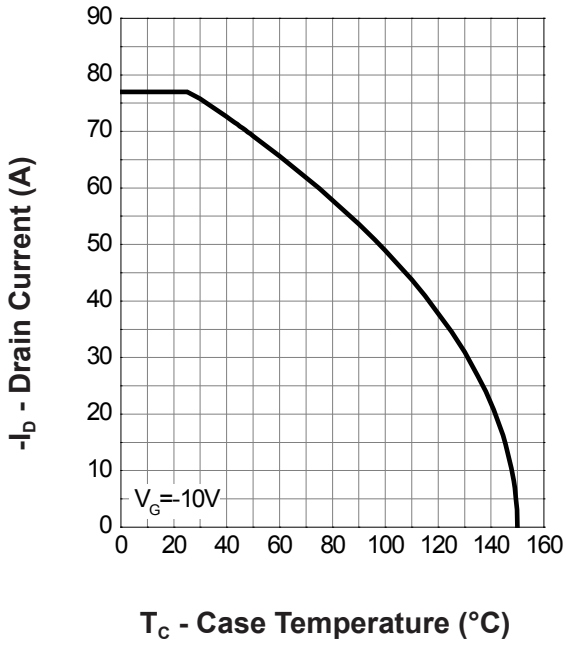


Typical Characteristics (Cont.)

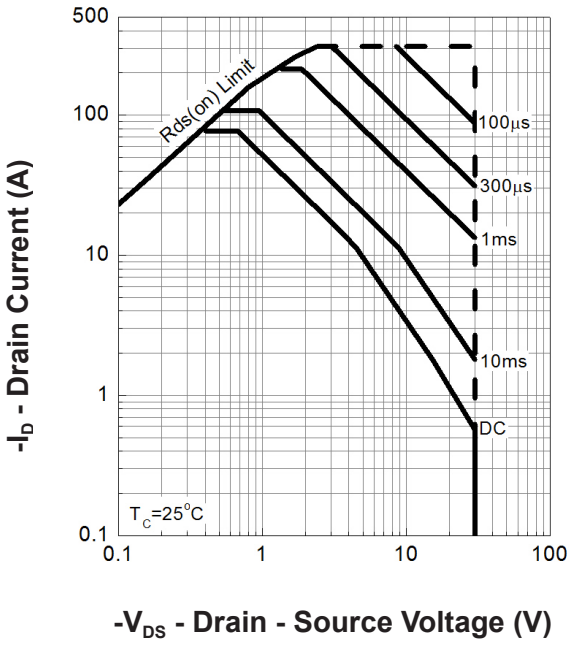
Power Dissipation



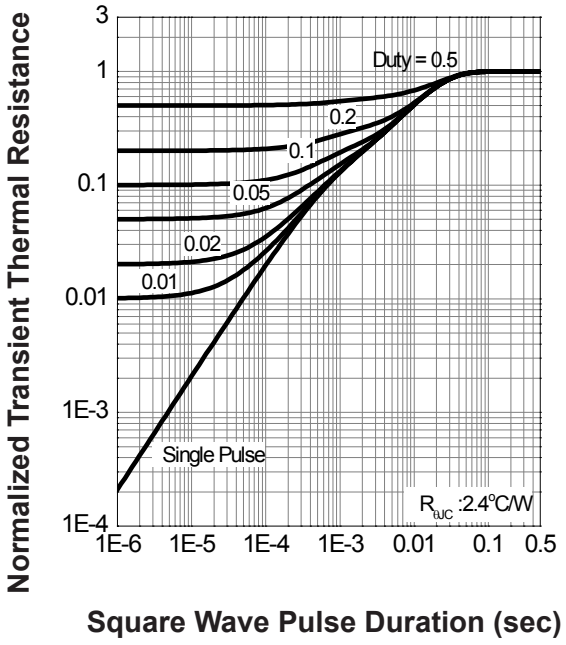
Drain Current



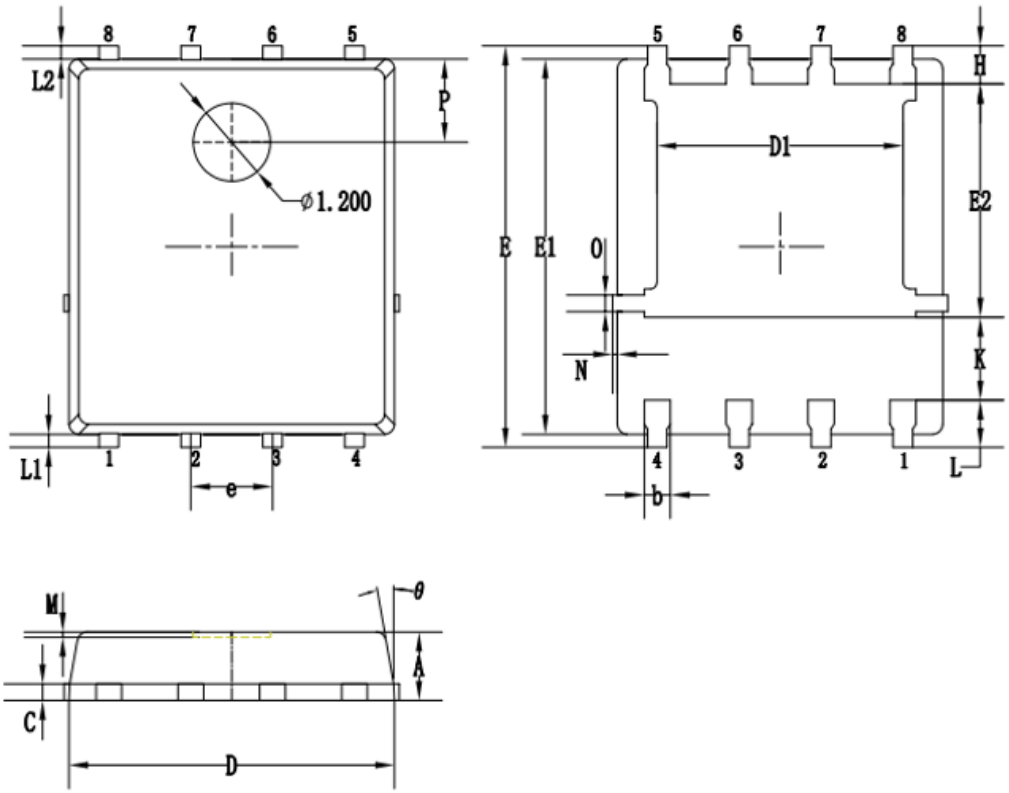
Safe Operation Area



Thermal Transient Impedance



Packaging information



SYMBOLS	MILLIMETERS		
	MIN.	NOM.	MAX.
A	0.90	1.05	1.20
b	0.35	0.40	0.50
C	0.20	0.25	0.35
D	4.90	5.05	5.20
D1	3.72	3.82	3.92
E	6.00	6.15	6.30
E1	5.60	5.75	5.90
E2	3.47	3.57	3.67
e	1.27 BSC.		
H	0.48	0.58	0.68
K	1.17	1.27	1.37
L	0.64	0.74	0.84
L1/L2	0.20 REF.		
θ	8°	10°	12°
M	0.08 REF.		
N	0	-	0.15
O	0.25 REF.		
P	1.28 REF.		

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